

RJK0349DSP

Silicon N Channel Power MOS FET Power Switching

REJ03G1659-0300 Rev.3.00 Jul 10, 2008

Features

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance $R_{DS(on)} = 2.9 \ m\Omega \ typ. \ (at \ V_{GS} = 10 \ V)$
- Pb-free

Outline

RENESAS Package code: PRSP0008DD-D (Package name: SOP-8<FP-8DAV>)

8765

BDDDDD

1, 2, 3 Source
4 Gate
5, 6, 7, 8 Drain

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	20	A
Drain peak current	I _{D(pulse)} Note1	160	A
Body-drain diode reverse drain current	I _{DR}	20	A
Avalanche current	I _{AP} Note 2	20	A
Avalanche energy	E _{AR} Note 2	40	mJ
Channel dissipation	Pch Note3	2.5	W
Channel to ambient thermal impedance	θch-a Note3	50	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tch = 25°C, Rg \geq 50 Ω
- 3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10s

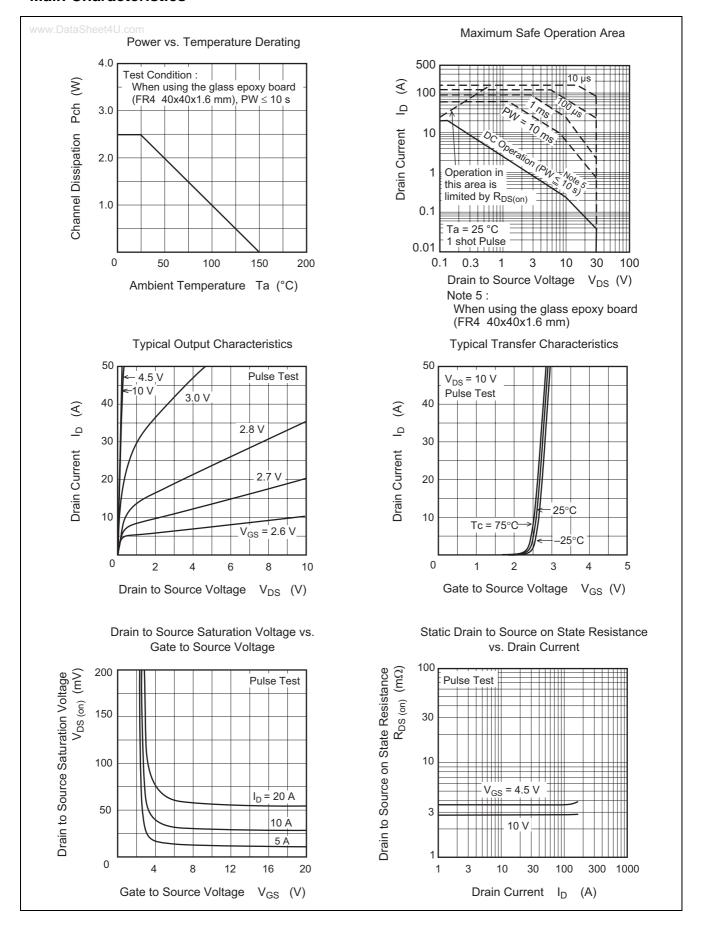
Electrical Characteristics

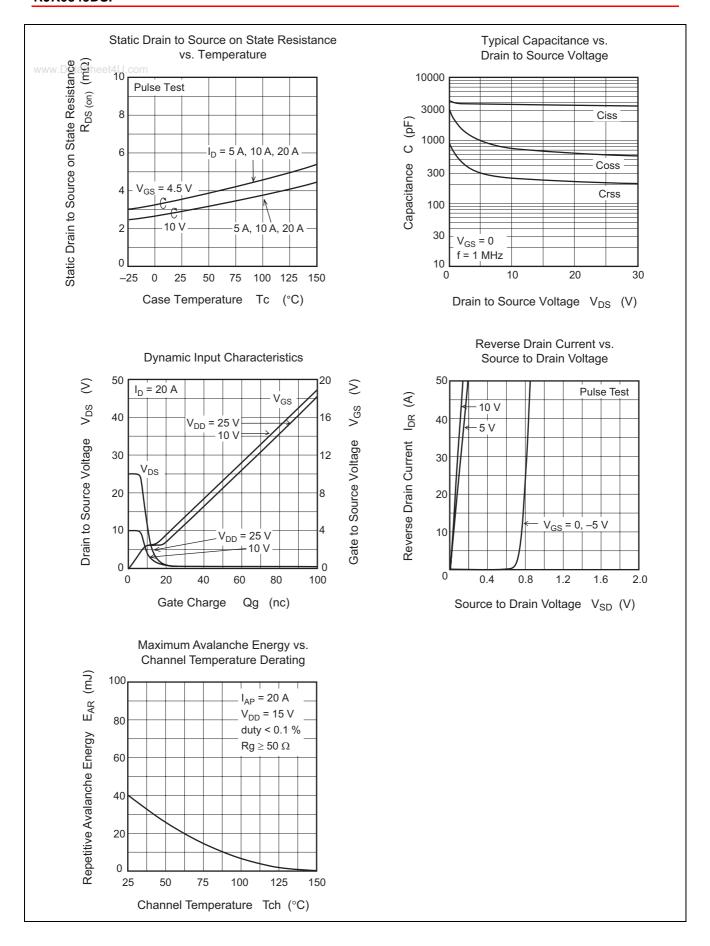
 $(Ta = 25^{\circ}C)$

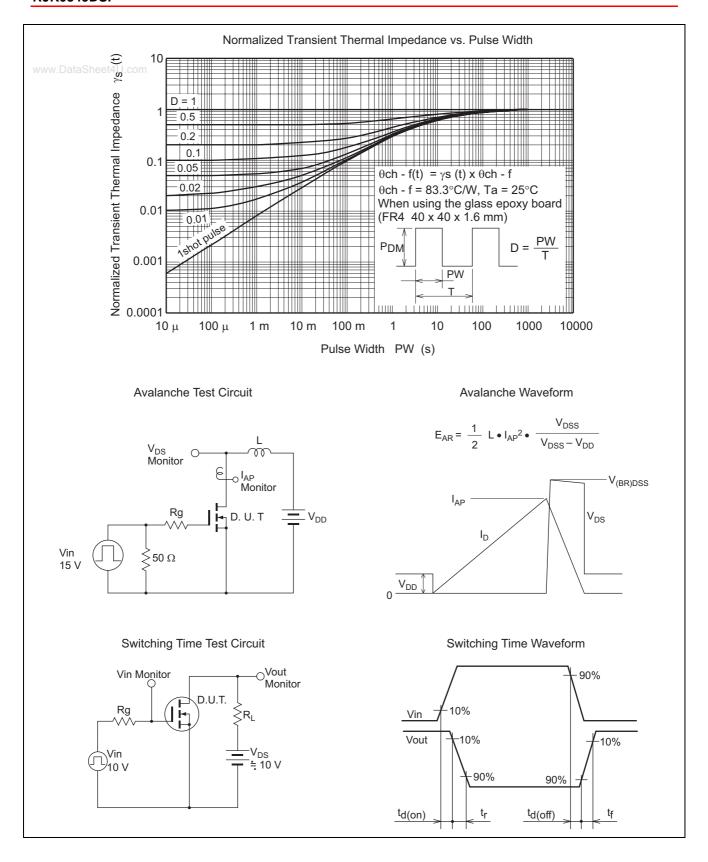
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.2	_	2.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	2.9	3.8	mΩ	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}	_	3.6	5.0	mΩ	$I_D = 10 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	_	55	_	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	3850	_	pF	V _{DS} = 10 V
Output capacitance	Coss	_	740	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	240	_	pF	f = 1 MHz
Gate Resistance	Rg	_	1.5	_	Ω	
Total gate charge	Qg	_	25	_	nC	V _{DD} = 10 V
Gate to source charge	Qgs	_	9.5	_	nC	V _{GS} = 4.5 V
Gate to drain charge	Qgd	_	5.3	_	nC	I _D = 20 A
Turn-on delay time	t _{d(on)}	_	11	_	ns	V _{GS} = 10 V, I _D = 10 A
Rise time	t _r	_	4.7	_	ns	V _{DD} ≅ 10 V
Turn-off delay time	t _{d(off)}	_	58.5	_	ns	$R_L = 1.00 \Omega$
Fall time	t _f	_	9.8	_	ns	$Rg = 4.7 \Omega$
Body-drain diode forward voltage	V_{DF}	_	0.78	1.02	V	$I_F = 20 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery	t _{rr}	_	30	_	ns	$I_F = 20 \text{ A}, V_{GS} = 0$
time						$di_F/dt = 100 A/\mu s$

Notes: 4. Pulse test

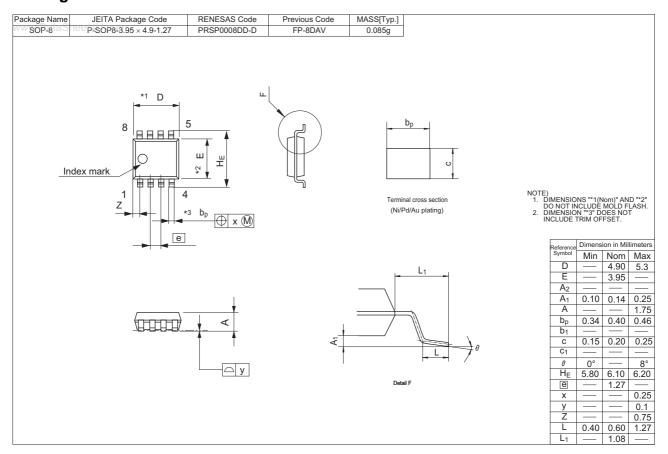
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK0349DSP-00-J0	2500 pcs	Taping

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510